Product data sheet

1. General description

PNP low V_{CEsat} transistor in a DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- · Reduced printed-circuit board requirements
- Leadless small SMD plastic package with solderable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint

3. Applications

- Loadswitch
 - Battery-driven devices
 - · Power management
 - Charging circuits
 - Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-2	Α
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -0.1 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	200	-	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	Е	emitter		С
3	С	collector	Transparent top view DFN2020D-3 (SOT1061D)	B — E sym132

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5250PAS	DFN2020D-3	plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); no leads; 3 terminals; 1.3 mm pitch; 2 mm x 2 mm x 0.65 mm body	<u>SOT1061D</u>

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5250PAS	G5

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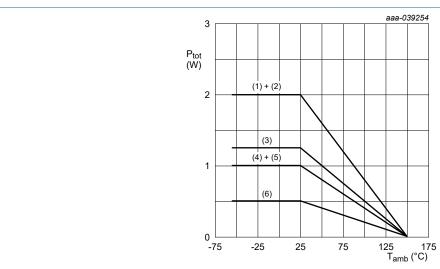
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V_{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	limited by T _{j(max)}		-	-5	А
I _B	base current			-	-0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.5	W
			[2] [3]	-	1	W
			[4]	-	1.2	W
			[5] [6]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃ standard footprint.
- [6] Device mounted on a FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².



- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from junction to ambient	[2 [4	[1]	-	-	250	K/W
			[2] [3]	-	-	125	K/W
			[4]	-	-	100	K/W
			[5] [6]	-	-	60	K/W

- Device mounted on an FR4 PCB, single-sided, 35 μ m copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided, 35 μ m copper, tin-plated, mounting pad for collector 1 cm². [2]
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm². [6]

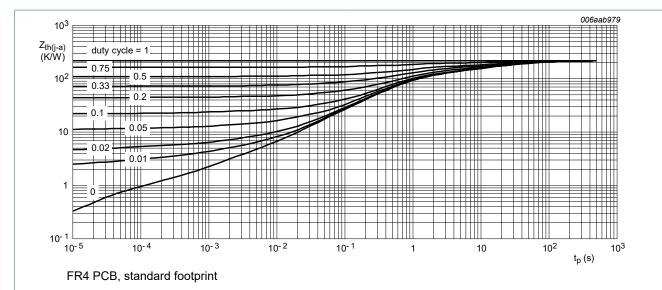
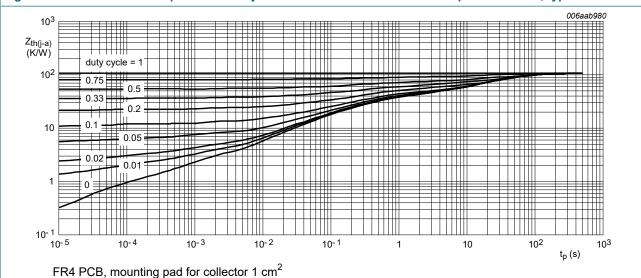


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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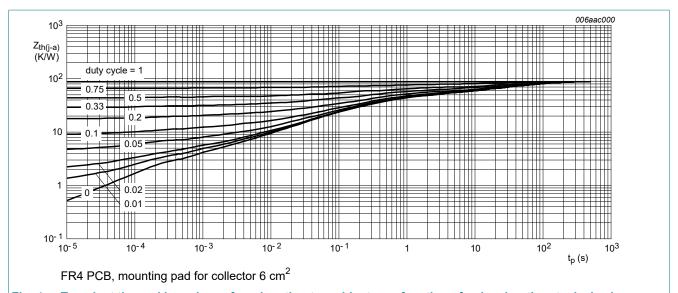


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

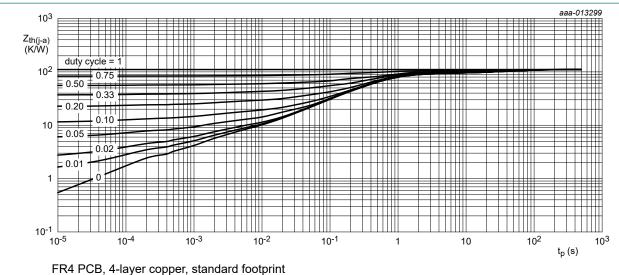


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

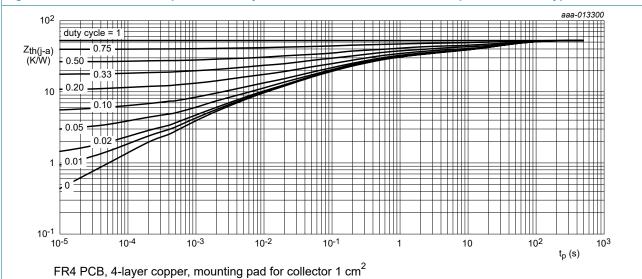
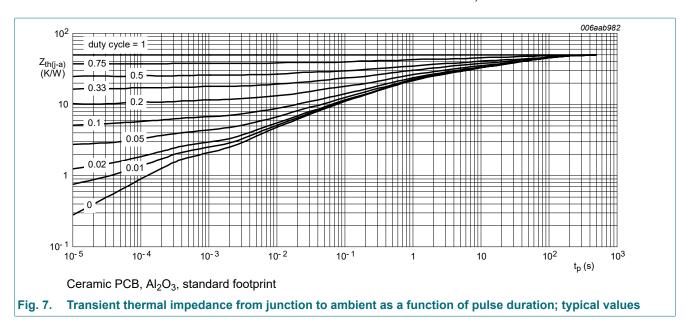


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	I_E = -100 μ A; I_C = 0 A; T_{amb} = 25 °C	-5	-	-	V
I _{CBO}	collector-base cut-off	$V_{CB} = -50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = -50 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -0.1 A; T _{amb} = 25 °C	200	-	-	
		V _{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter	$I_C = -0.5 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-90	mV
satu	saturation voltage	I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-250	mV
		$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-380	mV
		$I_C = -2 \text{ A}$; $I_B = -200 \text{ mA}$; pulsed; $t_p \le$	-	-	-320	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	160	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -2 A; I_B = -100 mA; T_{amb} = 25 °C	-	-	-1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	-1.1	-	-	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	-	35	pF

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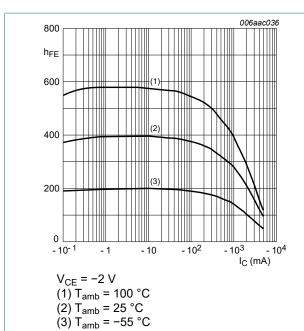


Fig. 8. DC current gain as a function of collector current; typical values

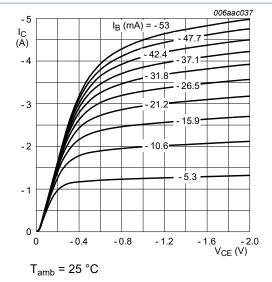
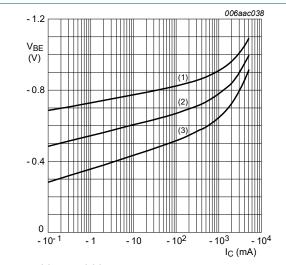
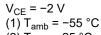


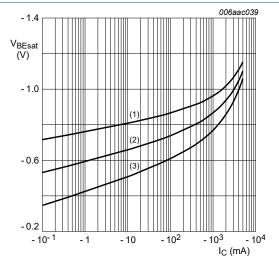
Fig. 9. Collector current as a function of collectoremitter voltage; typical values





(2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 10. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = -55$ °C (2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

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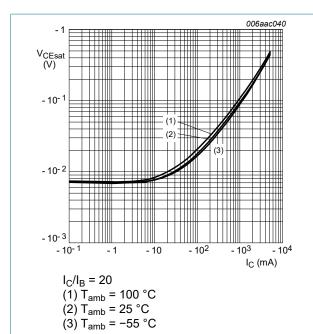


Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

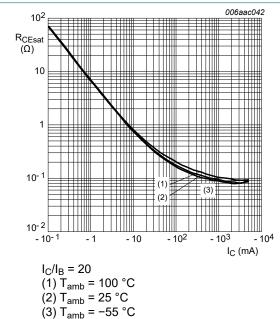


Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

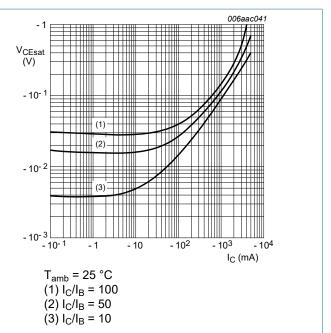
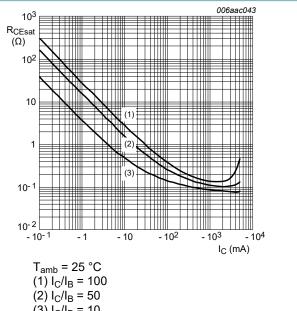


Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

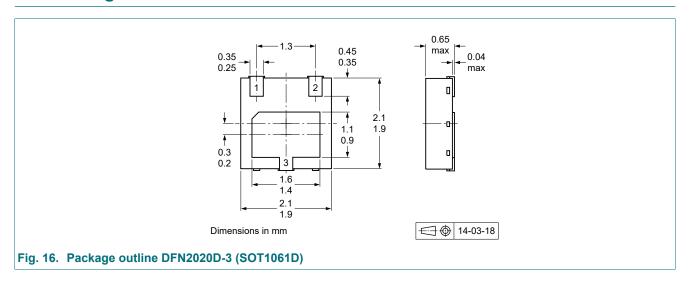


(3) $I_C/I_B = 10$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

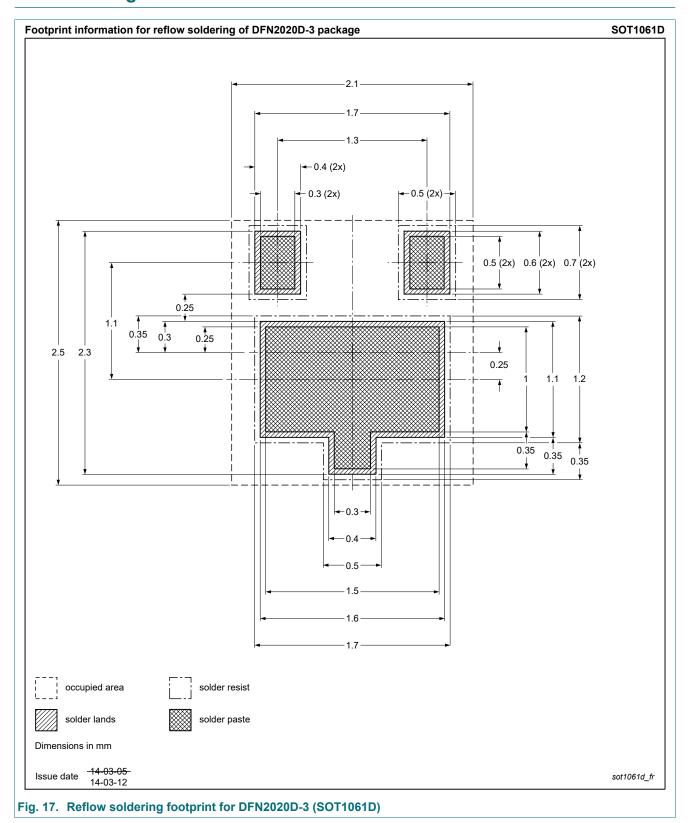
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11. Package outline



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12. Soldering



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13. Revision history

Table 8. Revision history

Table of Iteviolett Inletel	J			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5250PAS v.3	20240828	Product data sheet	-	PBSS5250PAS v.2
Modifications:	Pinning: Ty	po corrected		
PBSS5250PAS v.2	20240807	Product data sheet	-	PBSS5250PAS v.1
PBSS5250PAS v.1	20240516	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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